

CD4007UB Types

CMOS
Dual Complementary
Pair Plus Inverter

High-Voltage Types (20-Volt Rating)

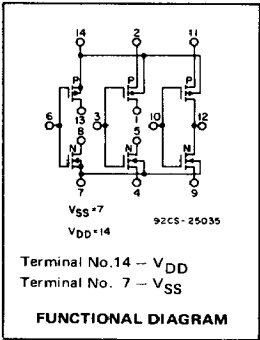
The RCA-CD4007UB types are comprised of three n-channel and three p-channel enhancement-type MOS transistors. The transistor elements are accessible through the package terminals to provide a convenient means for constructing the various typical circuits as shown in Fig. 2.

More complex functions are possible using multiple packages. Numbers shown in parentheses indicate terminals that are connected together to form the various configurations listed.

The CD4007UB types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Features:

- Standardized symmetrical output characteristics
- Medium Speed Operation — t_{PHL} , t_{PLH} = 30 ns (typ.) at 10 V
- 100% tested for quiescent current at 20 V
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C



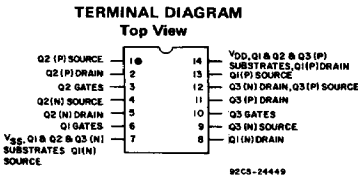
RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

Applications:

- Extremely high-input impedance amplifiers
- Shapers
- Inverters
- Threshold detector
- Linear amplifiers
- Crystal oscillators



STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
				Values at -55, +25, +125 Apply to D, F, K, H Packages Values at -40, +25, +85 Apply to E Package							
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	—	0,5	5	0.25	0.25	7.5	7.5	—	0.01	0.25	μA
	—	0,10	10	0.5	0.5	15	15	—	0.01	0.5	
	—	0,15	15	1	1	30	30	—	0.01	1	
	—	0,20	20	5	5	150	150	—	0.02	5	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	V
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, V _{IL} Max.	4.5	—	5	1				—	—	1	V
	9	—	10	2				—	—	2	
	13.5	—	15	2.5				—	—	2.5	
Input High Voltage, V _{IH} Min.	0.5	—	5	4				4	—	—	V
	1	—	10	8				8	—	—	
	1.5	—	15	12.5				12.5	—	—	
Input Current I _{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA

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MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V _{DD})	-0.5 to +20 V
(Voltages referenced to V _{SS} Terminal)	
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5 to V _{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT	±10 mA
POWER DISSIPATION PER-PACKAGE (P _D):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 12 mW/°C to 200 mW
For T _A = -55 to +100°C (PACKAGE TYPES D, F, K)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR T _A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPES D, F, K, H	-55 to +125°C
PACKAGE TYPE E	-40 to +85°C
STORAGE TEMPERATURE RANGE (T _{stg})	-65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max.	+265°C

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_r, t_f = 20 ns,
C_L = 50 pF, R_L = 200 KΩ

CHARACTERISTIC		CONDITIONS	ALL TYPES LIMITS		UNITS
			VDD Volts	Typ.	
Propagation Delay Time: tPHL, tPLH		5	55	110	ns
		10	30	60	
		15	25	50	
Transition Time tTHL, tTLH		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance	CIN	Any Input	10	15	pF

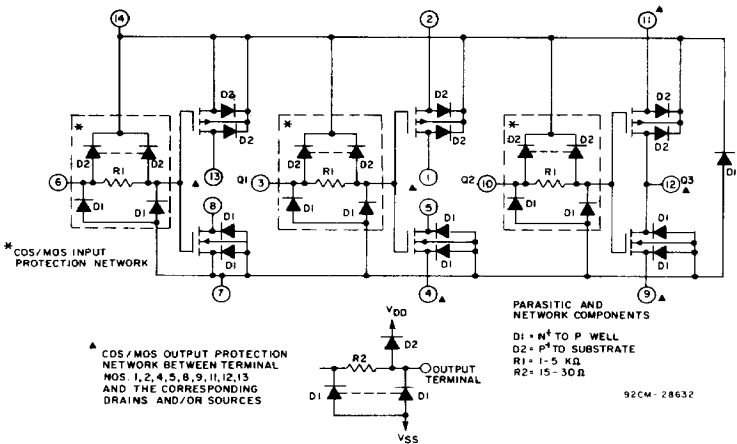
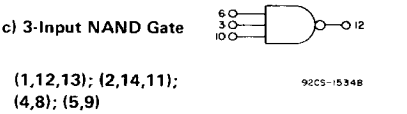
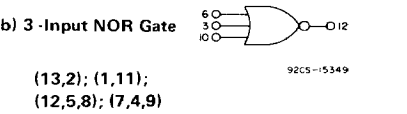
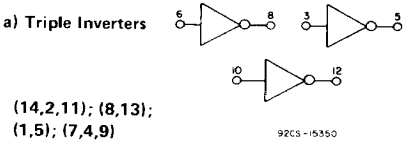


Fig. 1 — Detailed schematic diagram of CD4007UB showing input, output, and parasitic diodes.



d) Tree (Relay) Logic

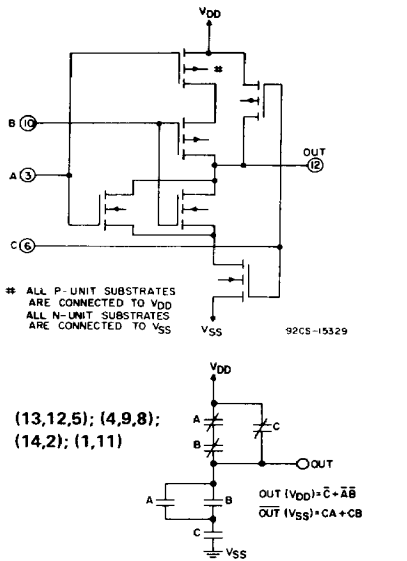
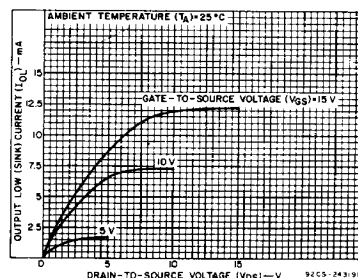
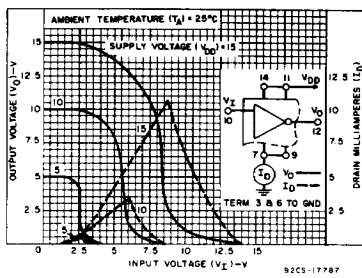
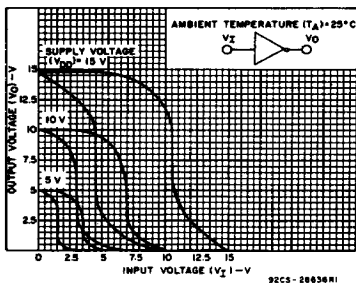
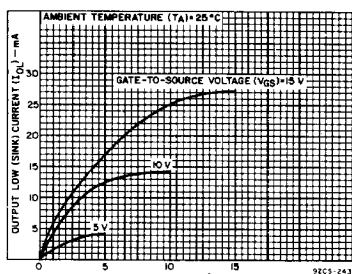
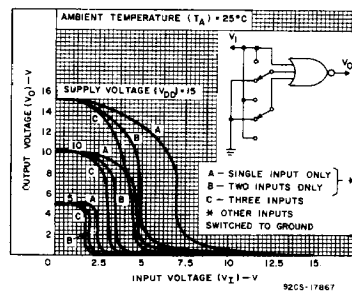
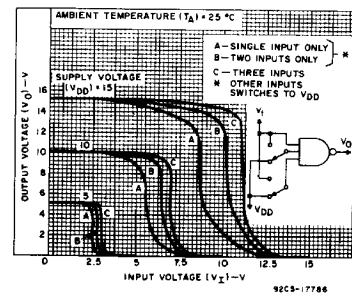
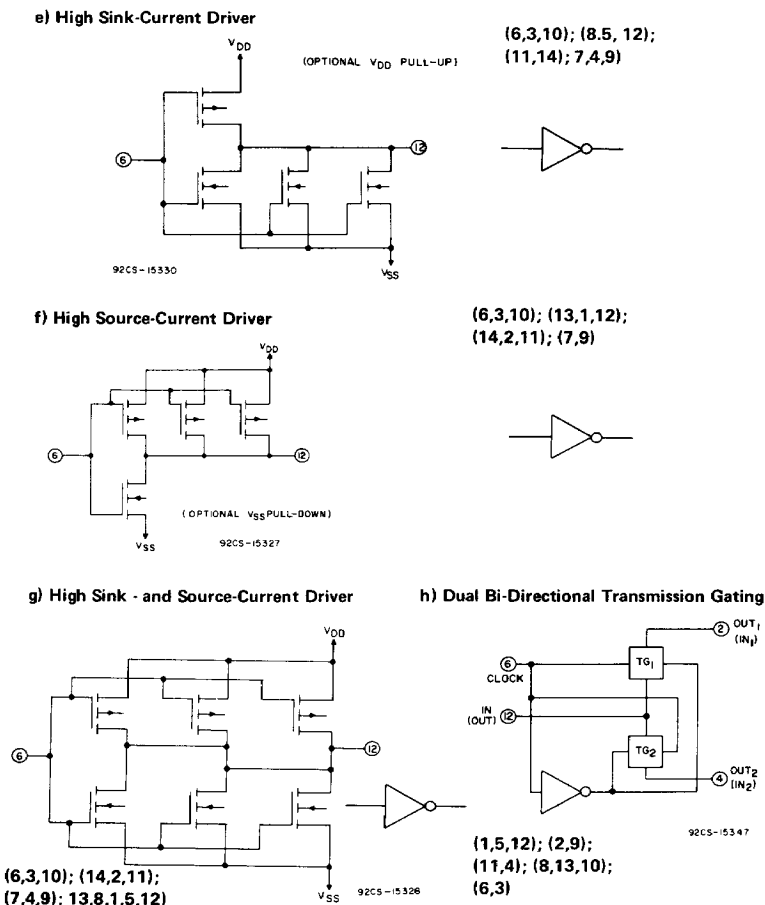


Fig. 2 — Sample COS/MOS logic circuit arrangements using type CD4007UB.

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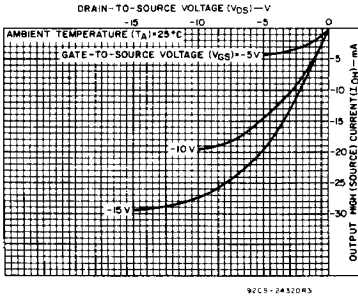


Fig. 9 - Typical output high (source) current characteristics.

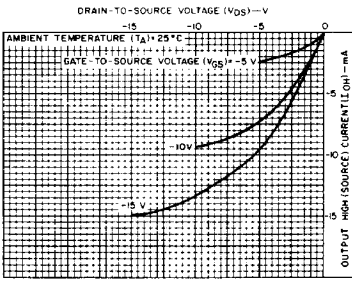


Fig. 10 - Minimum output high (source) current characteristics.

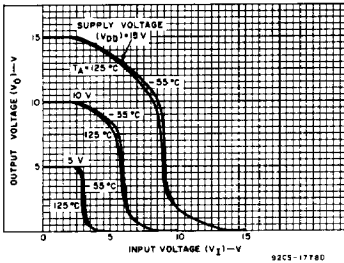


Fig. 11 - Typical voltage-transfer characteristics as a function of temperature.

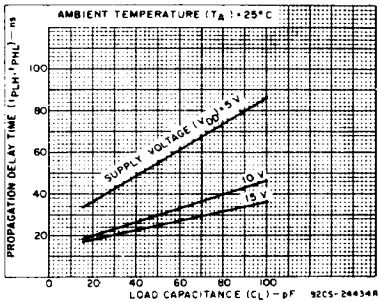


Fig. 12 - Typical propagation delay time vs. load capacitance.

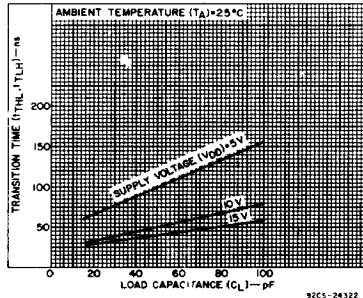


Fig. 13 - Typical transition time vs. load capacitance.

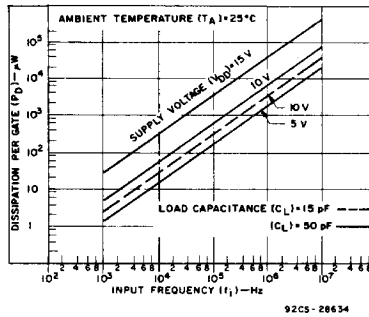


Fig. 14 - Typical dissipation vs. frequency characteristics.

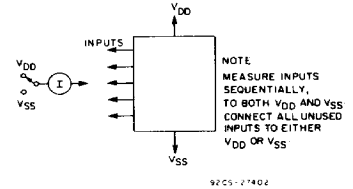


Fig. 15 - Input current test circuit.

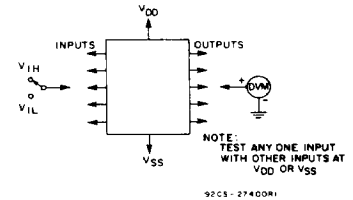


Fig. 16 - Input voltage test circuit.

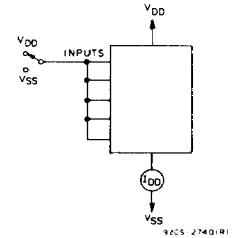
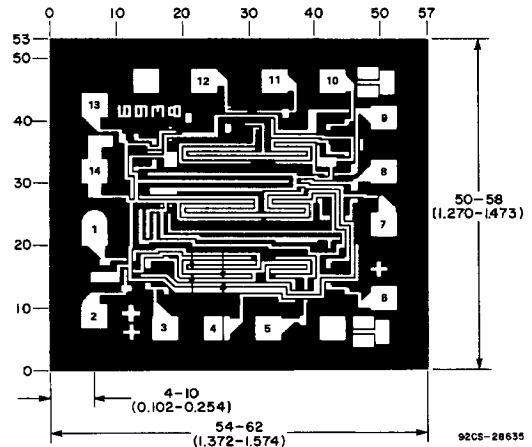


Fig. 17 - Quiescent device current test circuit.



DIMENSIONS AND PAD LAYOUT FOR CD4007UBH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of -3 mils to $+16$ mils applicable to the nominal dimensions shown.